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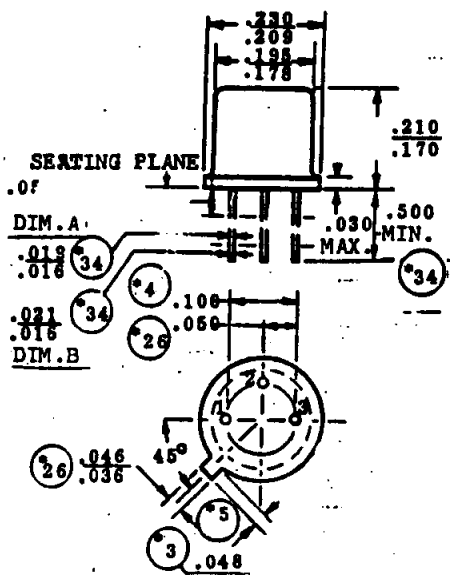
SPECIFICATIONS FOR 2N4340 AND 2N4341 (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions		Typ[a]	Limits 2N4340 Min	Limits 2N4340 Max	Limits 2N4341 Min	Limits 2N4341 Max	Unit
Static									
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = –1 μA, V_{DS} = 0 V		–57	–50		–50		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 15 V, I_D = 0.1 μA			–1	–3	–2	–6	V
Saturation Drain Current[b]	I_{DSS}	V_{DS} = 15 V, V_{GS} = 0 V			1.2	3.6	3	9	mA
Gate Reverse Current	I_{GSS}	V_{GS} = –30 V, V_{DS} = 0 V		–2		–100		–100	pA
			T_A = 150°C	–4		–100		–100	nA
Gate Operating Current[b]	I_G	V_{DG} = 15 V, I_D = 0.1 mA		–2					pA
Drain Cutoff Current	$I_{D(off)}$	V_{DS} = 15 V	V_{GS} = –5 V	2		50			pA
			V_{GS} = –10 V	3				70	pA
Gate-Source Forward Voltage	$V_{GS(F)}$	I_G = 1 mA, V_{DS} = 0 V		0.7					V

SPECIFICATIONS FOR 2N4340 AND 2N4341 (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Typ[a]	Limits 2N4340 Min	Limits 2N4340 Max	Limits 2N4341 Min	Limits 2N4341 Max	Unit
Dynamic								
Common-Source Forward Transconductance	g_{fs}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 kHz		1.3	3	2	4	mS
Common-Source Output Conductance	g_{os}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 kHz			30		60	μS
Drain-Source On-Resistance	$r_{ds(on)}$	V_{DS} = 0 V, V_{GS} = 0 V, f = 1 kHz			1500		800	Ω
Common-Source Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	5		7		7	pF
Common-Source Reverse Transfer Capacitance	C_{rss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	1.5		3		3	pF
Equivalent Input Noise Voltage[c]	$\bar{e}_n$	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 kHz	6					$\frac{nV}{\sqrt{Hz}}$
Noise Figure	NF	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 kHz, R_G = 1 MΩ			1		1	dB

Notes
a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
b. Pulse test: PW ≤300 μs, duty cycle ≤3%.
c. This parameter not registered with JEDEC.